



Contact Photolithography-Based Nanopatterning Using Photoresist Features Having Re-Entrant Profiles

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WARF: P180144US01

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The Invention

Patterning methods for forming patterned device substrates are provided. Also provided are devices made using the methods. The methods utilize photoresist features having re-entrant profiles to form a secondary metal hard mask that can be used to pattern an underlying device substrate.

Additional Information

For More Information About the Inventors

- [Zhenqiang Ma](#)

Tech Fields

- [Semiconductors & Integrated Circuits : Design & fabrication](#)

For current licensing status, please contact Jeanine Burmania at jeanine@warf.org or 608-960-9846